Atsushi Tsukazaki

List of Publications by Year
in descending order

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212 papers	14,123 citations	25034 57 h-index	21540 114 g-index
217 all docs	217 docs citations	217 times ranked	12418 citing authors

#	Article	IF	Citations
1	Experimental signature of the parity anomaly in a semi-magnetic topological insulator. Nature Physics, 2022, 18, 390-394.	16.7	45
2	Improvement of the detectivity in an Feâ€“Sn magnetic-field sensor with a large current injection. Japanese Journal of Applied Physics, 2022, 61, SC1069.	1.5	1
3	Quantum anomalous Hall effect with a permanent magnet defines a quantum resistance standard. Nature Physics, 2022, 18, 25-29.	16.7	31
4	Competing correlated states around the zero-field Wigner crystallization transition of electrons in two dimensions. Nature Materials, 2022, 21, 311-316.	27.5	25
5	L2₁ ordering of Co₂FeSn thin films promoted by high-temperature annealing. AIP Advances, 2022, 12, 065030.	1.3	0
6	Determination of the phase coherence length of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>PdCo</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> nanostructures by conductance fluctuation analysis. Physical Review B, 2021, 103, .	3.2	8
7	Giant anomalous Hall effect from spin-chirality scattering in a chiral magnet. Nature Communications, 2021, 12, 317.	12.8	40
8	Critical thickness for the emergence of Weyl features in Co3Sn2S2 thin films. Communications Materials, 2021, 2, .	6.9	23
9	Robust perpendicular magnetic anisotropy of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Co</mml:mi><mml:mn>3</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="normal">S</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> phase in sulfur deficient sputtered thin films. Physical Review Materials, 2021, 5, .	2.4	7
10	Current-induced switching of proximity-induced ferromagnetic surface states in a topological insulator. Nature Communications, 2021, 12, 1404.	12.8	47
11	First-principles investigation of magnetic and transport properties in hole-doped shandite compounds <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Co</mml:mi><mml:mn>3</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="normal">S</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2021, 103, .	3.2	21
12	Two-dimensionality of metallic surface conduction in Co3Sn2S2 thin films. Communications Physics, 2021, 4, .	5.3	7
13	Current-induced magnetization switching at charge-transferred interface between topological insulator (Bi,Sb)2Te3 and van der Waals ferromagnet Fe3GeTe2. Applied Physics Letters, 2021, 119, .	3.3	13
14	Versatile electronic states in epitaxial thin films of (Sn-Pb-In)Te: From topological crystalline insulator and polar semimetal to superconductor. Physical Review Materials, 2021, 5, .	2.4	2
15	Three-dimensional sensing of the magnetic-field vector by a compact planar-type Hall device. Communications Materials, 2021, 2, .	6.9	8
16	Nonreciprocal Transport in a Rashba Ferromagnet, Delafossite PdCoO₂. Nano Letters, 2021, 21, 8687-8692.	9.1	9
17	Magneto-optical spectroscopy on Weyl nodes for anomalous and topological Hall effects in chiral MnGe. Nature Communications, 2021, 12, 5974.	12.8	13
18	Tuning scalar spin chirality in ultrathin films of the kagome-lattice ferromagnet Fe3Sn. Communications Materials, 2021, 2, .	6.9	4

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19	Emergence of spin-orbit coupled ferromagnetic surface state derived from Zak phase in a nonmagnetic insulator FeSi. Science Advances, 2021, 7, eabj0498.	10.3	10
20	Formation of ilmenite-type single-crystalline MgTiO3 thin films by pulsed-laser deposition. AIP Advances, 2021, 11, .	1.3	4
21	Giant magneto-optical responses in magnetic Weyl semimetal Co3Sn2S2. Nature Communications, 2020, 11, 4619.	12.8	92
22	Large non-reciprocal charge transport mediated by quantum anomalous Hall edge states. Nature Nanotechnology, 2020, 15, 831-835.	31.5	20
23	Inhomogeneous interface dipole effect at the Schottky junctions of PdCrO2 on Î²-Ga2O3â€ˆ(2Â¯01) substrates. Journal of Applied Physics, 2020, 128, .	2.5	9
24	Current scaling of the topological quantum phase transition between a quantum anomalous Hall insulator and a trivial insulator. Physical Review B, 2020, 102, .	3.2	10
25	Stabilization of a honeycomb lattice of IrO6 octahedra by formation of ilmenite-type superlattices in MnTiO3. Communications Materials, 2020, 1, .	6.9	5
26	Single-domain formation of SrMnBi2 films on polar LaAlO3 substrate. AIP Advances, 2020, 10, 105216.	1.3	3
27	Direct Observation of the Statics and Dynamics of Emergent Magnetic Monopoles in a Chiral Magnet. Physical Review Letters, 2020, 125, 137202.	7.8	34
28	Microwave response of interacting oxide two-dimensional electron systems. Physical Review B, 2020, 102, .	3.2	3
29	Control of Schottky barrier height in metal/Î²-Ga2O3 junctions by insertion of PdCoO2 layers. APL Materials, 2020, 8, .	5.1	18
30	Signature of band inversion in the perovskite thin-film alloys <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>BaS</mml:mi><mml:msub><mml:mi mathvariant="normal">n</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â€“</mml:mo><mml:mi>x</mml:mi></mml:mrow><mml:mi mathvariant="normal">P</mml:mi><mml:msub><mml:mi mathvariant="normal">b</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>. Physi	3.2	10
31	Two-dimensional growth of conductive ultra-thin Sn films on insulating substrate with an Fe buffer layer. APL Materials, 2020, 8, 061103.	5.1	1
32	Electrical detection of the antiferromagnetic transition in MnTiO3 ultrathin films by spin Hall magnetoresistance. Journal of Applied Physics, 2020, 127, 103903.	2.5	8
33	Precise resistance measurement of quantum anomalous Hall effect in magnetic heterostructure film of topological insulator. Applied Physics Letters, 2020, 116, 143101.	3.3	17
34	Dynamic characteristics of PdCoO2/Î²-Ga2O3 Schottky junctions. Applied Physics Letters, 2020, 116, .	3.3	16
35	Magnetic-field-induced topological phase transition in Fe-doped <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mrow><mml:mo>(</mml:mo><mml:mrow><mml:mi mathvariant="normal">S</mml:mi><mml:msub><mml:mi mathvariant="normal">e</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow>	2.4	15
36	Anomalous Hall effect at the spontaneously electron-doped polar surface of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>PdCo</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> ultrathin films. Physical Review Research, 2020, 2, .	3.6	20

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37	Large Anomalous Hall Effect in Topological Insulators with Proximitized Ferromagnetic Insulators. Physical Review Letters, 2019, 123, 016804.	7.8	79
38	Electric dipole effect in PdCoO ₂ /Î²-Ga ₂ O ₃ Schottky diodes for high-temperature operation. Science Advances, 2019, 5, eaax5733.	10.3	59
39	Low-frequency noise measurements on Feâ€“Sn Hall sensors. Applied Physics Express, 2019, 12, 123001.	2.4	7
40	Ballistic transport in periodically modulated MgZnO/ZnO two-dimensional electron systems. Applied Physics Letters, 2019, 115, 153101.	3.3	6
41	Quantum anomalous Hall effect driven by magnetic proximity coupling in all-telluride based heterostructure. Applied Physics Letters, 2019, 115, .	3.3	67
42	Magnetic topological insulators. Nature Reviews Physics, 2019, 1, 126-143.	26.6	636
43	Nonreciprocal charge transport at topological insulator/superconductor interface. Nature Communications, 2019, 10, 2734.	12.8	72
44	Ferromagnetic Co₃Sn₂S₂ thin films fabricated by co-sputtering. Japanese Journal of Applied Physics, 2019, 58, 050912.	1.5	26
45	Quantized conductance of one-dimensional strongly correlated electrons in an oxide heterostructure. Physical Review B, 2019, 99, .	3.2	3
46	Publisher's Note: Topological spin-hedgehog crystals of a chiral magnet as engineered with magnetic anisotropy [Phys. Rev. B 96, 220414(R) (2017)]. Physical Review B, 2019, 99, .	3.2	0
47	Fe-Sn nanocrystalline films for flexible magnetic sensors with high thermal stability. Scientific Reports, 2019, 9, 3282.	3.3	26
48	Growth control of corundum-derivative MnSnO3 thin films by pulsed-laser deposition. AIP Advances, 2019, 9, 035210.	1.3	4
49	Thin-film stabilization of LiNbO3-type ZnSnO3 and MgSnO3 by molecular-beam epitaxy. APL Materials, 2019, 7, .	5.1	20
50	Formation of distorted rutile-type NbO2, MoO2, and WO2 films by reactive sputtering. Journal of Applied Physics, 2019, 125, .	2.5	14
51	Giant thermoelectric power factor in ultrathin FeSe superconductor. Nature Communications, 2019, 10, 825.	12.8	61
52	Doping-induced enhancement of anomalous Hall coefficient in Fe-Sn nanocrystalline films for highly sensitive Hall sensors. APL Materials, 2019, 7, .	5.1	9
53	Large magneto-thermopower in MnGe with topological spin texture. Nature Communications, 2018, 9, 408.	12.8	36
54	Fermi-level tuning of the Dirac surface state in (Bi_{1â^'x}Sb_x)₂Se₃thin films. Journal of Physics Condensed Matter, 2018, 30, 085501.	1.8	13

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55	Critical current enhancement driven by suppression of superconducting fluctuation in ion-gated ultrathin FeSe. Superconductor Science and Technology, 2018, 31, 055003.	3.5	4
56	Andreev Reflection at the Interface with an Oxide in the Quantum Hall Regime. Journal of the Physical Society of Japan, 2018, 87, 124712.	1.6	8
57	A cascade of phase transitions in an orbitally mixed half-filled Landau level. Science Advances, 2018, 4, eaat8742.	10.3	27
58	Pulsed-laser deposition of InSe thin films for the detection of thickness-dependent bandgap modification. Applied Physics Letters, 2018, 113, .	3.3	9
59	Current-driven magnetization switching in ferromagnetic bulk Rashba semiconductor (Ge,Mn)Te. Science Advances, 2018, 4, eaat9989.	10.3	28
60	Effect of the depletion region in topological insulator heterostructures for ambipolar field-effect transistors. Physical Review B, 2018, 98, .	3.2	7
61	Ferromagnetic insulator Cr2Ge2Te6 thin films with perpendicular remanence. APL Materials, 2018, 6, .	5.1	51
62	Emergence of interfacial conduction and ferromagnetism in MnTe/InP. Applied Physics Letters, 2018, 113, .	3.3	8
63	Topological quantum phase transition in magnetic topological insulator upon magnetization rotation. Physical Review B, 2018, 98, .	3.2	23
64	Anisotropy of the upper critical field and its thickness dependence in superconducting FeSe electric-double-layer transistors. Physical Review B, 2018, 97, .	3.2	9
65	High-mobility field-effect transistor based on crystalline ZnSnO3 thin films. AIP Advances, 2018, 8, .	1.3	6
66	Highly conductive PdCoO2 ultrathin films for transparent electrodes. APL Materials, 2018, 6, .	5.1	45
67	All-in-all-out magnetic domain inversion in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Tb</mml:mi><mml:mn>2</mml:mn></mml:mr mathvariant="normal">O</mml:mi><mml:mn>7</mml:mn></mml:msub></mml:mrow></mml:math> with molecular fields antiparallel to external fields. Physical Review Materials, 2018, 2, .	2.4	12
68	Enhancement of superconducting transition temperature in FeSe electric-double-layer transistor with multivalent ionic liquids. Physical Review Materials, 2018, 2, .	2.4	13
69	Microfabrication of SrRuO3 thin films on various oxide substrates using LaAlO3/BaOx sacrificial bilayers. , 2018, , .		2
70	Hall field-induced resistance oscillations in MgZnO/ZnO heterostructures. Physical Review B, 2017, 95, .	3.2	12
71	A magnetic heterostructure of topological insulators as a candidate for an axion insulator. Nature Materials, 2017, 16, 516-521.	27.5	276
72	Observation of anomalous Hall effect in a non-magnetic two-dimensional electron system. Nature Communications, 2017, 8, 14777.	12.8	35

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73	Enhanced electron mobility at the two-dimensional metallic surface of BaSnO3 electric-double-layer transistor at low temperatures. Applied Physics Letters, 2017, 110, .	3.3	26
74	Unified trend of superconducting transition temperature versus Hall coefficient for ultrathin FeSe films prepared on different oxide substrates. Physical Review B, 2017, 95, .	3.2	19
75	Alloy disorder modulated electron transport at MgxZn1-xO/ZnO heterointerface. AIP Advances, 2017, 7, 015029.	1.3	2
76	Tailoring tricolor structure of magnetic topological insulator for robust axion insulator. Science Advances, 2017, 3, eaao1669.	10.3	155
77	Current-Nonlinear Hall Effect and Spin-Orbit Torque Magnetization Switching in a Magnetic Topological Insulator. Physical Review Letters, 2017, 119, 137204.	7.8	122
78	A versatile patterning process based on easily soluble sacrificial bilayers. AIP Advances, 2017, 7, .	1.3	11
79	Nonlinear response of a MgZnO/ZnO heterostructure close to zero bias. Physical Review B, 2017, 96, .	3.2	1
80	Visualizing ferroic domains in an all-inâ€“all-out antiferromagnet thin film. Physical Review B, 2017, 96, .	3.2	5
81	Quantized chiral edge conduction on domain walls of a magnetic topological insulator. Science, 2017, 358, 1311-1314.	12.6	112
82	Current-Driven Instability of the Quantum Anomalous Hall Effect in Ferromagnetic Topological Insulators. Physical Review Letters, 2017, 119, 016803.	7.8	30
83	Observation of superparamagnetism in coexistence with quantum anomalous Hall Câ€‰=â€‰Â±1 and Câ€‰=â€‰0 Chern states. Npj Quantum Materials, 2017, 2, .	5.2	23
84	Topological spin-hedgehog crystals of a chiral magnet as engineered with magnetic anisotropy. Physical Review B, 2017, 96, .	3.2	25
85	Fabrication of tetragonal FeSeâ€“FeS alloy films with high sulfur contents by alternate deposition. Japanese Journal of Applied Physics, 2017, 56, 100308.	1.5	11
86	Improvement of electron mobility in La:BaSnO3 thin films by insertion of an atomically flat insulating (Sr,Ba)SnO3 buffer layer. AIP Advances, 2016, 6, .	1.3	55
87	Co thin films deposited directly on ZnO polar surfaces. Scientific Reports, 2016, 6, 38005.	3.3	13
88	Observation of the quantum Hall effect in Î´-doped SrTiO3. Nature Communications, 2016, 7, 11631.	12.8	62
89	High field-effect mobility at the (Sr,Ba)SnO3/BaSnO3 interface. AIP Advances, 2016, 6, 085014.	1.3	16
90	Zero-bias photocurrent in ferromagnetic topological insulator. Nature Communications, 2016, 7, 12246.	12.8	22

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91	All-in-all-out magnetic domain size in pyrochlore iridate thin films as probed by local magnetotransport. Applied Physics Letters, 2016, 108, .	3.3	23
92	Direct observation of anisotropic magnetic field response of the spin helix in FeGe thin films. Physical Review B, 2016, 94, .	3.2	24
93	Large Unidirectional Magnetoresistance in a Magnetic Topological Insulator. Physical Review Letters, 2016, 117, 127202.	7.8	144
94	Fermi-level-dependent charge-to-spin current conversion by Dirac surface states of topologicalÂinsulators. Nature Physics, 2016, 12, 1027-1031.	16.7	307
95	Observation of microwave induced resistance and photovoltage oscillations in MgZnO/ZnO heterostructures. Physical Review B, 2016, 93, .	3.2	30
96	All-in-all-out magnetic domain wall conduction in a pyrochlore iridate heterointerface. Physical Review B, 2016, 93, .	3.2	26
97	Enhanced photogalvanic current in topological insulators via Fermi energy tuning. Physical Review B, 2016, 93, .	3.2	84
98	Terahertz spectroscopy on Faraday and Kerr rotations in a quantum anomalous Hall state. Nature Communications, 2016, 7, 12245.	12.8	122
99	MgZnO/ZnO heterostructures with electron mobility exceeding 1â€‰Ã—â€‰106â€‰cm2/Vs. Scientific Reports, 2016, 6, 26598.	3.3	71
100	Quantum Hall effect in a bulk antiferromagnet EuMnBi ₂ with magnetically confined two-dimensional Dirac fermions. Science Advances, 2016, 2, e1501117.	10.3	171
101	Geometric Hall effects in topological insulatorÂheterostructures. Nature Physics, 2016, 12, 555-559.	16.7	146
102	Electric-field-induced superconductivity in electrochemically etched ultrathin FeSe filmsÂonÂSrTiO3 and MgO. Nature Physics, 2016, 12, 42-46.	16.7	227
103	Electrochemical-Etching Approach to Achieving Ultrathin FeSe Films. Hyomen Kagaku, 2016, 37, 541-546.	0.0	0
104	Topological Hall effect in thin films of the Heisenberg ferromagnet EuO. Physical Review B, 2015, 91, .	3.2	63
105	Magnetic Field-Induced Insulator-Semimetal Transition in a Pyrochlore<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>Nd</mml:mi></mml:mrow><mml:mrow><mml:mn>2</mml:mn></mml:mrow></mml:msub><mml:msub><mml:mrow><mml:mi mathvariant="normal">O</mml:mi></mml:mrow><mml:mrow><mml:mn>7</mml:mn></mml:mrow></mml:msub></mml:mrow>	7.8	86
106	Spin-Selective Electron Quantum Transport in Nonmagnetic<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>MgZnO</mml:mi><mml:mo>/</mml:mo><mml:mi>ZnO</mml:mi></mml:mrow></mml:math>H Physical Review Letters, 2015, 115, 197601.	7.8	12
107	Magnetic modulation doping in topological insulators toward higher-temperature quantum anomalous Hall effect. Applied Physics Letters, 2015, 107, .	3.3	260
108	Quantum Hall states stabilized in semi-magnetic bilayers of topological insulators. Nature Communications, 2015, 6, 8530.	12.8	53

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109	Formation of In-plane Skyrmions in Epitaxial MnSi Thin Films as Revealed by Planar Hall Effect. Journal of the Physical Society of Japan, 2015, 84, 104708.	1.6	40
110	Microwave magnetoplasma resonances of two-dimensional electrons in MgZnO/ZnO heterojunctions. Physical Review B, 2015, 91, .	3.2	22
111	Calibration and control of in-plane Mg doping distribution in MgxZn1â^'xO/ZnO heterostructures grown by molecular beam epitaxy. Japanese Journal of Applied Physics, 2015, 54, 028004.	1.5	2
112	Discretized topological Hall effect emerging from skyrmions in constricted geometry. Physical Review B, 2015, 91, .	3.2	84
113	Odd-parity magnetoresistance in pyrochlore iridate thin films with broken time-reversal symmetry. Scientific Reports, 2015, 5, 9711.	3.3	68
114	Even-denominator fractional quantum Hall physics in ZnO. Nature Physics, 2015, 11, 347-351.	16.7	138
115	Quantum Hall effect on top and bottom surface states of topological insulator (Bi1â^'xSbx)2Te3 films. Nature Communications, 2015, 6, 6627.	12.8	154
116	Optical probing of MgZnO/ZnO heterointerface confinement potential energy levels. Applied Physics Letters, 2015, 106, .	3.3	23
117	Electron scattering times in ZnO based polar heterostructures. Applied Physics Letters, 2015, 107, .	3.3	36
118	Polarization-dependent Landau level crossing in a two-dimensional electron system in a MgZnO/ZnO heterostructure. Physical Review B, 2014, 90, .	3.2	26
119	Enhanced quantum oscillatory magnetization and nonequilibrium currents in an interacting two-dimensional electron system in MgZnO/ZnO with repulsive scatterers. Physical Review B, 2014, 89, .	3.2	0
120	Air-gap gating of MgZnO/ZnO heterostructures. Journal of Applied Physics, 2014, 116, 084310.	2.5	2
121	Spontaneous polarization driven Mg concentration profile reconstruction in MgZnO/ZnO heterostructures. Applied Physics Letters, 2014, 104, 242112.	3.3	3
122	Photoinduced sign inversion of the anomalous Hall effect in EuO thin films. Physical Review B, 2014, 89, .	3.2	7
123	Dirac electron states formed at the heterointerface between a topological insulator and a conventional semiconductor. Nature Materials, 2014, 13, 253-257.	27.5	66
124	Challenges and opportunities of ZnO-related single crystalline heterostructures. Applied Physics Reviews, 2014, 1, 011303.	11.3	118
125	Stability of two-dimensional skyrmions in thin films of Mn<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>Fe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>Si investigated by the topological Hall effect. Physical Review B, 2014, 89, .	3.2	73
126	Trajectory of the anomalous Hall effect towards the quantized state in a ferromagnetic topological insulator. Nature Physics, 2014, 10, 731-736.	16.7	517

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127	Surface and interface engineering of ZnO based heterostructures fabricated by pulsed-laser deposition. Journal Physics D: Applied Physics, 2014, 47, 034003.	2.8	11
128	Systematic control of stress-induced anisotropy in pseudomorphic iron garnet thin films. Journal of Magnetism and Magnetic Materials, 2013, 339, 63-70.	2.3	54
129	Observation of plasma and magnetoplasma resonances of two-dimensional electrons in a single MgZnO/ZnO heterojunction. JETP Letters, 2013, 98, 223-226.	1.4	2
130	Robust Formation of Skyrmions and Topological Hall Effect Anomaly in Epitaxial Thin Films of MnSi. Physical Review Letters, 2013, 110, 117202.	7.8	269
131	Rashba spin-orbit interaction in a Mg<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>Zn<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>O/ZnO [illegible] spin resonance. Physical Review B, [illegible]	3.2	25
132	Magneto-photoluminescence of charged excitons from Mg<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>Zn<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>O/ZnO heterojunctions. Physical Review B, 2013, 87, .	3.2	12
133	[illegible] Mg<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>Zn<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>O/ZnO strongly correlated two-dimensional electron system. Physical Review B, 2012, 85, .	3.2	36
134	Ultrafast Time-Resolved Faraday Rotation in EuO Thin Films. Physical Review Letters, 2012, 108, 257401.	7.8	23
135	Gate control of surface transport in MBE-grown topological insulator (Bi1â^’xSbx)2Te3thin films. Physical Review B, 2012, 86, .	3.2	24
136	Temperature-Dependent Magnetotransport around<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>Î½</mml:mi><mml:mo>=</mml:mo><mml:mn>1</mml:mn><mml:mo>/</mml:mo><mml:mn>2</mml:mn>< [illegible] ZnO Heterostructures. Physical Review Letters, 2012, 108, 186803.	7.8	31
137	Correlation-Enhanced Effective Mass of Two-Dimensional Electrons in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>Mg</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi>Zn</mml:mi><mml:mr [illegible] mathvariant="normal">O</mml:mi><mml:mo>/</mml:mo><mml:mi>ZnO</mml:mi></mml:math>Heterostructures. Physical Review Letters, 2012, 109, 246401.	7.8	23
138	Stress-Induced Perpendicular Magnetization in Epitaxial Iron Garnet Thin Films. Applied Physics Express, 2012, 5, 103002.	2.4	82
139	Ultrafast optical control of magnetization in EuO thin films. Physical Review B, 2012, 86, .	3.2	14
140	Precise calibration of Mg concentration in Mg<i>x</i>Zn1â^’<i>x</i>O thin films grown on ZnO substrates. Journal of Applied Physics, 2012, 112, .	2.5	16
141	Magnesium Doping Controlled Density and Mobility of Two-Dimensional Electron Gas in Mg$_{x}$Zn$_{1-x}$O/ZnO Heterostructures. Applied Physics Express, 2011, 4, 091101.	2.4	72
142	Pulsed Laser Deposition and Ionic Liquid Gate Control of Epitaxial Bi$_{2}$Se$_{3}$ Thin Films. Applied Physics Express, 2011, 4, 083001.	2.4	52
143	Observation of anomalous Hall effect in EuO epitaxial thin films grown by a pulse laser deposition. Applied Physics Letters, 2011, 98, .	3.3	37
144	Second and Third-Order Nonlinear Optical Effects in ZnO Channel Waveguides. , 2011, , .		0

#	Article	IF	Citations
145	Fabrication of ZnO channel waveguides for nonlinear optical applications. Proceedings of SPIE, 2011, , .	0.8	0
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